

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Hisashi OHTANI et al.

Serial No. 08/807,737

Filed: February 27, 1997

For: METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE) Group Art Unit: 2829
) Examiner: Evan T. PERT
)
) Date: March 3, 2003RECEIVED
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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on March 3, 2003.

Deborah Movahhedi
Deborah Movahhedi

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EX-1
March
3/4/03

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 2, 2002, please consider the following amendments and remarks in connection with the above-identified application.

03/04/2003 SZEWDIE1 00000058 08807737

03 FC:1202

CP
IN THE CLAIMS:

Please amend claims 60, 61, 73, and 84 as follows:

60. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate by using a CVD system;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

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02 FC:1201

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